

| L Number | Hits | Search Text | DB | Time stamp |
|----------|-------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------|------------------|
| 5 | 10425 | programm\$3 and (float\$3 adj3 gate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:46 |
| 6 | 8958 | (programm\$3 and (float\$3 adj3 gate)) and (memory adj3 cell) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:46 |
| 7 | 5260 | ((programm\$3 and (float\$3 adj3 gate)) and (memory adj3 cell)) and ("bit line" or "column line") | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:47 |
| 8 | 5196 | ((((programm\$3 and (float\$3 adj3 gate)) and (memory adj3 cell)) and ("bit line" or "column line")) and (transistor or (source or drain)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:47 |
| 9 | 991 | ((((programm\$3 and (float\$3 adj3 gate)) and (memory adj3 cell)) and ("bit line" or "column line")) and (transistor or (source or drain))) and (power or voltage or potential) and pre\$1charg\$2 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:48 |
| 10 | 178 | (((((programm\$3 and (float\$3 adj3 gate)) and (memory adj3 cell)) and ("bit line" or "column line")) and (transistor or (source or drain))) and (power or voltage or potential) and pre\$1charg\$2) and (reference adj2 current) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:48 |
| 11 | 165 | (((((programm\$3 and (float\$3 adj3 gate)) and (memory adj3 cell)) and ("bit line" or "column line")) and (transistor or (source or drain))) and (power or voltage or potential) and pre\$1charg\$2) and (reference adj2 current) and ("word line" or "row line") | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:49 |
| 12 | 154 | (((((((programm\$3 and (float\$3 adj3 gate)) and (memory adj3 cell)) and ("bit line" or "column line")) and (transistor or (source or drain))) and (power or voltage or potential) and pre\$1charg\$2) and (reference adj2 current)) and ("word line" or "row line")) and ("sense amplifier" or amplifier) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:50 |
| 13 | 145 | (((((((programm\$3 and (float\$3 adj3 gate)) and (memory adj3 cell)) and ("bit line" or "column line")) and (transistor or (source or drain))) and (power or voltage or potential) and pre\$1charg\$2) and (reference adj2 current)) and ("word line" or "row line")) and ("sense amplifier" or amplifier)) and 365/\$7.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:50 |
| 15 | 18 | (((((((programm\$3 and (float\$3 adj3 gate)) and (memory adj3 cell)) and ("bit line" or "column line")) and (transistor or (source or drain))) and (power or voltage or potential) and pre\$1charg\$2) and (reference adj2 current)) and ("word line" or "row line")) and ("sense amplifier" or amplifier)) and 365/203.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:50 |

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| 16 | 14 | (((((programm\$3 and (float\$3 adj3 gate)) and (memory adj3 cell)) and ("bit line" or "column line")) and (transistor or (source or drain))) and (power or voltage or potential) and pre\$1charg\$2) and (reference adj2 current)) and ("word line" or "row line")) and ("sense amplifier" or amplifier)) and 365/210.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:51 |
| 17 | 2 | (((((programm\$3 and (float\$3 adj3 gate)) and (memory adj3 cell)) and ("bit line" or "column line")) and (transistor or (source or drain))) and (power or voltage or potential) and pre\$1charg\$2) and (reference adj2 current)) and ("word line" or "row line")) and ("sense amplifier" or amplifier)) and 365/185.14.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:51 |
| 18 | 31 | (((((programm\$3 and (float\$3 adj3 gate)) and (memory adj3 cell)) and ("bit line" or "column line")) and (transistor or (source or drain))) and (power or voltage or potential) and pre\$1charg\$2) and (reference adj2 current)) and ("word line" or "row line")) and ("sense amplifier" or amplifier)) and 365/185.14.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:53 |
| 14 | 31 | (((((programm\$3 and (float\$3 adj3 gate)) and (memory adj3 cell)) and ("bit line" or "column line")) and (transistor or (source or drain))) and (power or voltage or potential) and pre\$1charg\$2) and (reference adj2 current)) and ("word line" or "row line")) and ("sense amplifier" or amplifier)) and 365/185.25.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:55 |
| 19 | 26 | marotta-giulio.in. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:55 |
| 20 | 18 | vali-tomaso.in. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:56 |
| 21 | 3 | "6687161" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 10:57 |
| 22 | 0 | 20020172076.URPN. | USPAT | 2004/06/10 10:57 |
| 23 | 0 | 20020172076.URPN. | USPAT | 2004/06/10 10:57 |